L Number	Hits	Search Text	DB	Time stamp
_	155637	polysi or polysilicon or (poly or	USPAT;	2004/08/10 13:43
		polycrystal\$5) adj (si or silicon)	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	656558	stress\$4	USPAT;	2004/08/10 09:04
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	3947590	annoaléd on hoatéd on thormalé2 adi2	IBM_TDB USPAT;	2004/08/10 13:48
	3947390	anneal\$4 or heat\$4 or thermal\$3 adj3	US-PGPUB;	2004/00/10 13:46
1		1	EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	878976	gate	USPAT;	2004/08/10 13:45
			US-PGPUB;	[
			EPO; JPO; DERWENT;	
			IBM TDB	
l –	718828	oxidi\$5 or oxidat\$5	USPAT;	2004/08/10 11:33
			US-PGPUB;	
			EPO; JPO;	
		r ·	DERWENT;	
_	30152	(oxidi\$5 or oxidat\$5) same (polysi or	USPAT;	2004/08/10 09:10
	50102	polysilicon or (poly or polycrystal\$5) adj	US-PGPUB;	
		(si or silicon))	EPO; JPO;	
			DERWENT;	
	114220		IBM_TDB USPAT;	2004/08/10 09:10
_	114339	stress\$4 same (anneal\$4 or heat\$4 or thermal\$3 adj3 treat\$5)	USPAT; US-PGPUB;	2004/08/10 09:10
		thermalys adjo treatys/	EPO; JPO;	:
	:		DERWENT;	
			IBM_TDB	
-	956		USPAT;	2004/08/10 09:12
		polysilicon or (poly or polycrystal\$5) adj (si or silicon))) and (stress\$4 same	US-PGPUB; EPO; JPO;	
		(anneal\$4 or heat\$4 or thermal\$3 adj3	DERWENT;	
		treat\$5)) and gate	IBM TDB	
-	2478932	tungsten or w	USPĀT;	2004/08/10 13:57
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	643	(((oxidi\$5 or oxidat\$5) same (polysi or	USPAT;	2004/08/10 09:24
		polysilicon or (poly or polycrystal\$5) adj	US-PGPUB;	
	•	(si or silicon))) and (stress\$4 same	EPO; JPO;	
		(anneal\$4 or heat\$4 or thermal\$3 adj3 treat\$5)) and gate) and (tungsten or w)	DERWENT; IBM TDB	
_	19778	creat(\$5)) and gate) and (tungsten of w)   gate with stack\$4	USPAT;	2004/08/10 09:26
		<b></b>	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	182	//ovidits or ovidatts) came /polygi or	IBM_TDB USPAT;	2004/08/10 11:32
-	182	((oxidi\$5 or oxidat\$5) same (polysi or polysilicon or (poly or polycrystal\$5) adj	USPAT; US-PGPUB;	2004/00/10 11:32
		(si or silicon))) and (stress\$4 same	EPO; JPO;	
		(anneal\$4 or heat\$4 or thermal\$3 adj3	DERWENT;	
		treat\$5)) and (gate with stack\$4)	IBM_TDB	0004/00/10 11
-	2513		USPAT;	2004/08/10 10:06
		438/595.ccls.	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	546619	defect or trap	USPAT;	2004/08/10 11:32
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
L <u></u>		<u> </u>	I TOM INR	

_	6508889	suppress\$4 or reduc\$4 or decreas\$4	USPAT; US-PGPUB;	2004/08/10 11:34
			EPO; JPO;	
			DERWENT;	
l _	720568	oxidi\$5 or oxidat\$5 or reoxidi\$5 or	IBM_TDB USPAT;	2004/08/10 13:43
-	/20300	reoxidat\$5	US-PGPUB;	2004/00/10 13:43
		1001144070	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	7352191	suppress\$4 or reduc\$4 or decreas\$4 or	USPAT;	2004/08/10 11:34
		releas\$5	US-PGPUB;	
			EPO; JPO; DERWENT;	,
			IBM TDB	
-	50316	(anneal\$4 or heat\$4 or thermal\$3 adj3	USPAT;	2004/08/10 11:37
		treat\$5) same (suppress\$4 or reduc\$4 or	US-PGPUB;	
		decreas\$4 or releas\$5) same (oxidi\$5 or	EPO; JPO;	
		oxidat\$5 or reoxidi\$5 or reoxidat\$5)	DERWENT;	
	30328	oxidi\$5 or oxidat\$5 or reoxidi\$5 or	IBM_TDB USPAT;	2004/08/10 11:37
-	30326	reoxidat\$5) same (polysi or polysilicon or	US-PGPUB;	2004/06/10 11:3/
		(poly or polycrystal\$5) adj (si or	EPO; JPO;	
1		silicon))	DERWENT;	
			IBM_TDB	
-	1857	((anneal\$4 or heat\$4 or thermal\$3 adj3	USPAT;	2004/08/10 11:37
		treat\$5) same (suppress\$4 or reduc\$4 or	US-PGPUB;	
		decreas\$4 or releas\$5) same (oxidi\$5 or oxidat\$5 or reoxidi\$5 or reoxidat\$5)) and	EPO; JPO; DERWENT;	
		((oxidi\$5 or oxidat\$5 or reoxidi\$5 or	IBM TDB	
		reoxidat\$5) same (polysi or polysilicon or	15.1_105	
		(poly or polycrystal\$5) adj (si or		,
		silicon))) and gate		
-	720568	oxidi\$5 or oxidat\$5 or reoxidi\$5 or	USPAT;	2004/08/10 14:51
		reoxidat\$5	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	155637	polysi or polysilicon or (poly or	USPĀT;	2004/08/10 13:45
		polycrystal\$5) adj (si or silicon)	US-PGPUB;	
			EPO; JPO;	
	†		DERWENT; IBM TDB	
_	878976	gate	USPAT;	2004/08/10 13:46
			US-PGPUB;	
	•		EPO; JPO;	
	]		DERWENT;	
	1502126	buide on diguide on Maio ant ON and	IBM_TDB	2004/08/10 13:47
-	1523136	oxide or dioxide or "sio.sub.2" or "sio.sub2."	USPAT; US-PGPUB;	2004/00/10 13:4/
		310.3ub2.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2738813	sidewall or side adj2 wall or edge	USPAT;	2004/08/10 13:48
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	3947590	anneal\$4 or heat\$4 or thermal\$3 adj3	USPAT;	2004/08/10 13:49
		treat\$5	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1_	30115	(oxidi\$5 or oxidat\$5 or reoxidi\$5 or	IBM_TDB USPAT;	2004/08/10 13:51
	30113	reoxidat\$5 ) near10 ((polysi or	US-PGPUB;	2004/00/10 13.31
		polysilicon or (poly or polycrystal\$5) adj	EPO; JPO;	
		(si or silicon) ) or gate )	DERWENT;	
			IBM_TDB	

-	35576	(oxide or dioxide or "sio.sub.2" or "sio.sub2.") near10 (sidewall or side adj2 wall or edge)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/10 13:53
-	9036	<pre>((oxidi\$5 or oxidat\$5 or reoxidi\$5 or reoxidat\$5 ) near10 ((polysi or polysilicon or (poly or polycrystal\$5) adj (si or silicon) ) or gate )) and ((oxide or dioxide or "sio.sub.2" or "sio.sub2.") near10 (sidewall or side adj2 wall or edge))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:54
-	3276		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:56
-	512		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:56
_	2478932		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:57
_	11519	<pre>(polysi or polysilicon or (poly or polycrystal\$5) adj (si or silicon) ) same gate same (tungsten or w )</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/10 13:58
-	141	<pre>((((oxidi\$5 or oxidat\$5 or reoxidi\$5 or reoxidat\$5 ) near10 ((polysi or polysilicon or (poly or polycrystal\$5) adj (si or silicon) ) or gate )) same ((oxide or dioxide or "sio.sub.2" or "sio.sub2.") near10 (sidewall or side adj2 wall or edge))) same (anneal\$4 or heat\$4 or thermal\$3 adj3 treat\$5 )) and ((polysi or polysilicon or (poly or polycrystal\$5) adj (si or silicon) ) same gate same (tungsten or w ))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 14:50
	141	<pre>(tungsten or w )) (((((oxidi\$5 or oxidat\$5 or reoxidi\$5 or reoxidat\$5 ) near10 ((polysi or polysilicon or (poly or polycrystal\$5) adj (si or silicon) ) or gate )) same ((oxide or dioxide or "sio.sub.2" or "sio.sub2.") near10 (sidewall or side adj2 wall or edge))) same (anneal\$4 or heat\$4 or thermal\$3 adj3 treat\$5 )) and ((polysi or polysilicon or (poly or polycrystal\$5) adj (si or silicon) ) same gate same (tungsten or w ))) and (anneal\$4 or heat\$4 or thermal\$3 adj3 treat\$5 )</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 14:21
_	8935	selectivi\$4 near3 (oxidi\$5 or oxidat\$5) or reoxidi\$5 or reoxidat\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 14:53
_	635	<pre>(selectivi\$4 near3 (oxidi\$5 or oxidat\$5) or reoxidi\$5 or reoxidat\$5 ) near15 ((polysi or polysilicon or (poly or polycrystal\$5) adj (si or silicon) ) or gate )</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 14:55

	19977	(oxide or dioxide or "sio.sub.2" or	USPAT;	2004/08/10 14:59
_	1 19977	"sio.sub2.") near20 ((sidewall or side	US-PGPUB;	2004/08/10 14:59
		adj2 wall or edge) or side adj2 surface)	EPO; JPO;	
		near20 ((polysi or polysilicon or (poly or	DERWENT;	
		polycrystal\$5) adj (si or silicon) ) or	IBM TDB	
		polycrystal 33 ) add (SI of Silicon)	TEM_TOB	
l <u> </u>	116	-	USPAT:	2004/08/10 14:59
	110	or reoxidi\$5 or reoxidat\$5 ) near15	US-PGPUB;	2004/08/10 14.59
		((polysi or polysilicon or (poly or	EPO; JPO;	
		(\(\frac{1}{1}\)\ \(\frac{1}{1}\)\ \(\frac{1}\)\ \(\frac{1}\)\ \(\frac{1}\)\ \(\frac{1}\)\ \(\frac{1}\)\ \(\frac{1}{1}\)\ \(\frac{1}\)\ \	DERWENT;	
		gate )) same ((oxide or dioxide or	IBM TDB	
		"sio.sub.2" or "sio.sub2.") near20	1561_155	
		((sidewall or side adj2 wall or edge) or		
	1	side adj2 surface) near20 ((polysi or		
		polysilicon or (poly or polycrystal\$5) adj		
		(si or silicon) ) or gate ))		
_	78		USPAT:	2004/08/10 15:48
		or reoxidi\$5 or reoxidat\$5 ) near15	US-PGPUB;	2001, 00, 20 20, 10
	1	((polysi or polysilicon or (poly or	EPO; JPO;	
		polycrystal\$5) adj (si or silicon) ) or	DERWENT;	
		gate )) same ((oxide or dioxide or	IBM TDB	
		"sio.sub.2" or "sio.sub2.") near20		
		((sidewall or side adj2 wall or edge) or		
		side adj2 surface) near20 ((polysi or		
		polysilicon or (poly or polycrystal\$5) adj		
		(si or silicon) ) or gate ))) and		
		(anneal\$4 or heat\$4 or thermal\$3 adj3		
		treat\$5 )		
-	1105	438/592.ccls.	USPAT;	2004/08/10 15:49
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	

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